

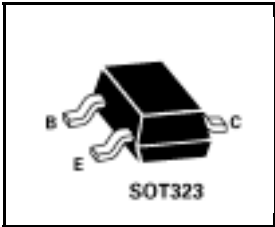
SOT323 PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

ISSUE 2 – FEBRUARY 1999

PARTMARKING DETAILS ZUMT807-25 - T8
 ZUMT807-40 - T24

COMPLEMENTARY TYPES ZUMT807-25 - ZUMT817-25
 ZUMT807-40 - ZUMT817-40

ZUMT807-25
ZUMT807-40



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-1	A
Continuous Collector Current	I_C	-500	mA
Base Current	I_B	-100	mA
Peak Base Current	I_{BM}	-200	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	330	mW
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector Cut-Off Current	I_{CBO}			-0.1 -5	μA μA	$V_{CB}=-20V, I_E=0$ $V_{CB}=-20V, I_E=0, T_{amb}=150^{\circ}C$
Emitter Cut-Off Current	I_{EBO}			-10	μA	$V_{EB}=-5V, I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-700	mV	$I_C=-500mA, I_B=-50mA^*$
Base-Emitter Turn-on Voltage	$V_{BE(on)}$			-1.2	V	$I_C=-500mA, V_{CE}=-1V^*$
Static Forward Current Transfer Ratio	h_{FE}	100 40		600		$I_C=-100mA, V_{CE}=-1V^*$ $I_C=-500mA, V_{CE}=-1V^*$
	-25	160		400		$I_C=-100mA, V_{CE}=-1V^*$
	-40	250		600		$I_C=-100mA, V_{CE}=-1V^*$
Transition Frequency	f_T		100		MHz	$I_C=-10mA, V_{CE}=-5V$ $f=35MHz$
Collector-base Capacitance	C_{obo}		8.0		pF	$I_E=I_C=0, V_{CB}=-10V$ $f=1MHz$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$